Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSⅢ)

2SK4034

Switching Regulator, DC-DC Converter Applications Motor Drive Applications

Low drain-source ON-resistance: R_{DS} (ON) = 4.2 mΩ(typ.)

• High forward transfer admittance: |Y_{fs}| = 110 S (typ.)

• Low leakage current: I_{DSS} = 100 μA (V_{DS} = 60 V)

• Enhancement mode: V_{th} = 1.5 to 2.5 V (V_{DS} = 10 V, I_D = 1 mA)

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit | |
|--|--------------------------------|------------------|------------|------|--|
| Drain-source voltage | | V_{DSS} | 60 | V | |
| Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$) | | V_{DGR} | 60 | V | |
| Gate-source voltage | | V_{GSS} | ±20 | V | |
| Drain current | DC (Note 1) | I _D | 75 | | |
| | Pulse (t \leq 1 ms) (Note 1) | I _{DP} | 300 | Α | |
| Drain power dissipat | ion (Tc = 25°C) | P_{D} | 125 | W | |
| Single pulse avalanche energy (Note 2) | | E _{AS} | 322 | mJ | |
| Avalanche current | | I _{AR} | 75 | Α | |
| Repetitive avalanche energy (Note 3) | | E _{AR} | 12.5 | mJ | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature range | | T _{stg} | -55 to 150 | °C | |

9.2 max 7.0±0.2 7.0±0.2 1.0±0.21.0±0.2 3.6 ± 0.2 1.0±0.21.0±0.2 3.6 ± 0.2 4. DRAIN : D JEDEC JEITA SC-97 TOSHIBA 2-9F1B

Weight: 0.74 g (typ.)

Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|-------------------------------------|------------------------|-----|------|
| Thermal resistance, channel to case | R _{th (ch-c)} | 1.0 | °C/W |

Note: Use the S1 pin to return the gate signal to source. Board traces should be designed so the main current flows to the S2 pin.

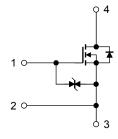
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), $L = 78 \mu\text{H}$, $R_G = 25 \Omega$, $I_{AR} = 75 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

Note 4: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



This transistor is an electrostatic-sensitive device. Handle with care.

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Electrical Characteristics (Note 5) (Ta = 25°C)

| Ch | aracteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------------------|-----------------------|--|-----|-------|-----|------|
| Gate leakage cui | rent | I _{GSS} | $V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±10 | μА |
| Drain cut-off curr | ent | I _{DSS} | V _{DS} = 60 V, V _{GS} = 0 V | _ | _ | 100 | μΑ |
| Drain-source breakdown voltage | | V _{(BR) DSS} | $I_D = 10$ mA, $V_{GS} = 0$ V | 60 | _ | _ | V |
| | | V _{(BR) DSX} | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 35 | _ | _ | V |
| Gate threshold v | oltage | V _{th} | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$ | 1.5 | _ | 2.5 | V |
| Drain-source ON-resistance | | R _{DS} (ON) | V _{GS} = 10 V, I _D = 38 A | _ | 4.2 | 5.8 | mΩ |
| | | | V _{GS} = 4.5 V, I _D = 38 A | _ | 5.5 | 10 | mΩ |
| Forward transfer admittance | | Y _{fs} | V _{DS} = 10 V, I _D = 38 A | 55 | 110 | _ | S |
| Input capacitance | | C _{iss} | | _ | 12400 | _ | pF |
| Reverse transfer capacitance | | C _{rss} | $V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | _ | 410 | _ | |
| Output capacitance | | Coss | | _ | 1100 | _ | |
| Switching time | Rise time | t _r | V _{GS} 10 V | _ | 15 | _ | - ns |
| | Turn-on time | t _{on} | | _ | 35 | _ | |
| | Fall time | t _f | VDD ≈ 30V | _ | 45 | _ | |
| | Turn-off time | t _{off} | Duty ≤ 1%, t _W = 10 μs | _ | 250 | _ | |
| Total gate charge (gate-source plus gate-drain) | | Qg | V _{DD} ≈ 48 V, V _{GS} = 10 V, | _ | 196 | _ | |
| Gate-source charge | | Q _{gs} | $I_D = 75 \text{ A}$ | _ | 148 | _ | nC |
| Gate-drain ("mille | Gate-drain ("miller") charge | | | _ | 48 | _ | |

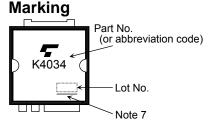
Note 5: The S1 and S2 pins should be grounded together, except when measuring the switching time.

Source-Drain Ratings and Characteristics (Note 6) (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|--------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1, Note 6) | I _{DR} 1 | _ | _ | _ | 75 | Α |
| Pulse drain reverse current (Note 1, Note 6) | I _{DRP} 1 | _ | _ | _ | 300 | Α |
| Continuous drain reverse current (Note 1, Note 6) | I _{DR} 2 | _ | _ | _ | 1 | Α |
| Pulse drain reverse current (Note 1, Note 6) | I _{DRP} 2 | _ | _ | _ | 4 | Α |
| Forward voltage (diode) | V _{DS2F} | I _{DR1} = 75 A, V _{GS} = 0 V | _ | _ | -1.5 | V |
| Reverse recovery time | t _{rr} | $I_{DR} = 75 \text{ A}, V_{GS} = 0 \text{ V},$ $dI_{DR}/dt = 50 \text{ A/}\mu\text{s}$ | _ | 70 | _ | ns |
| Reverse recovery charge | Q _{rr} | | _ | 77 | _ | nC |

Note 6: I_{DR}1, I_{DRP}1: Current flowing between the drain and S2 pins. Ensure that the S1 pin is left open. I_{DR}2, I_{DRP}2: Current flowing between the drain and S1 pins. Ensure that the S2 pin is left open.

The S1 and S2 pins should be grounded together, unless otherwise noted.



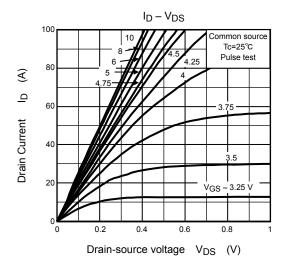
Note 7: A line under a Lot No. identifies the indication of product Labels.

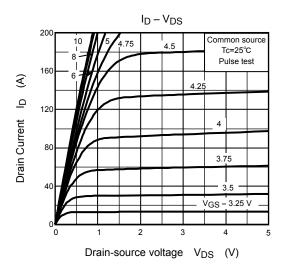
Not underlined: [[Pb]]/INCLUDES > MCV

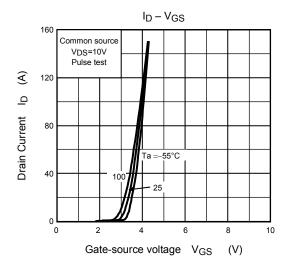
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

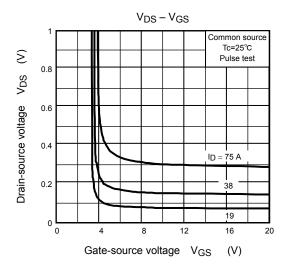
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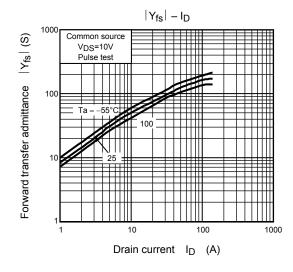
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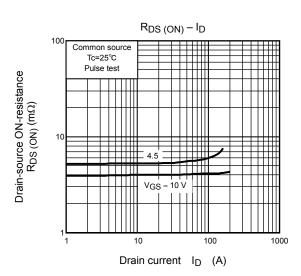


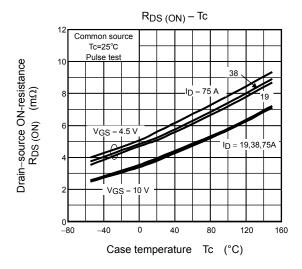


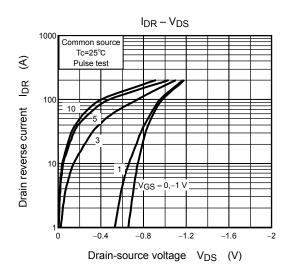


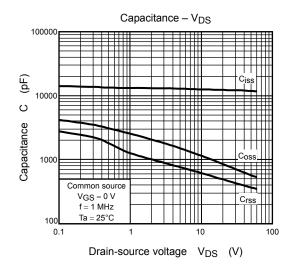


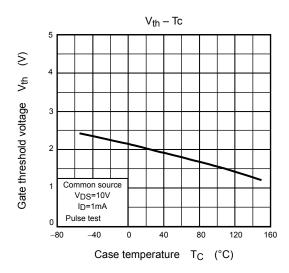


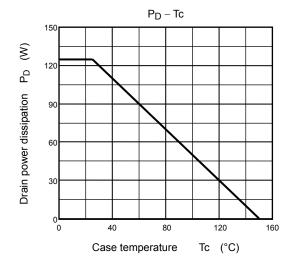


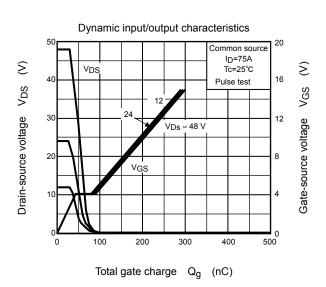


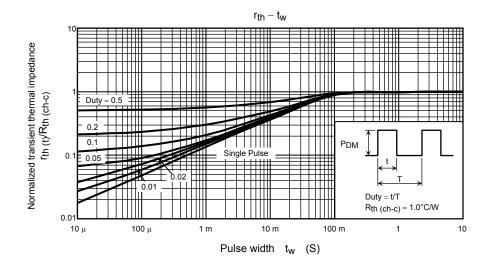


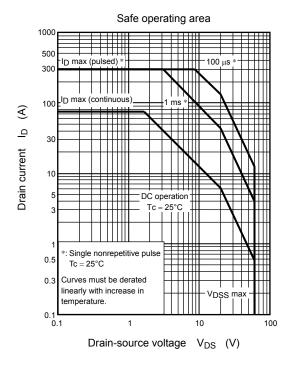


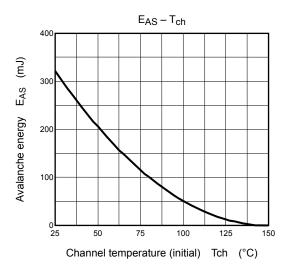


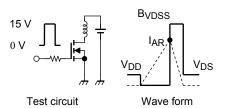












$$\begin{aligned} R_G &= 25 \ \Omega \\ V_{DD} &= 25 \ V, \ L = 78 \ \mu H \end{aligned} \qquad E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right) \end{aligned}$$

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